	Type	L #	Hits	Search Text	DBs
1	BRS	L2	33	"5124568" "5,731,716" "6,331,949" "6,590,825" "6,654,272" "6,693,819" 2002/0122331 2005/0149896	USPAT
2	IS&R	L3	6	(("5,124,568") or ("5,731,716") or ("6,331,949") or ("6,590,825") or ("6,654,272") or ("6,693,819")).PN. or ((2002/0122331) or (2005/0149896)).CCLS.	USPAT
3	IS&R	L4	6	(("5,124,568") or ("5,731,716") or ("6,331,949") or ("6,590,825") or ("6,654,272") or ("6,693,819")).PN. or ((2002/0122331) or (2005/0149896)).CCLS.	US-PGPUB; USPAT
4	IS&R	L5	8	(("5,124,568") or ("5,731,716") or ("6,331,949") or ("6,590,825") or ("6,654,272") or ("6,693,819") or ("20020122331") or ("20050149896")).PN.	US-PGPUB; USPAT
5	IS&R	L6	8	(("5124568") or ("5731716") or ("6331949") or ("6590825") or ("6654272") or ("6693819") or ("20020122331") or ("20050149896")).PN.	US-PGPUB; USPAT
6	BRS	L1	3610172	"5", "124,568" "5,731,716" "6,33" "1,949" "6,590,825" "6,654,272" "6,693,8" "19" 2002/0122331 2005/0149896	USPAT
7	BRS	L7	12735	diode same ((second or plurality) adj (pFET$1 or transistor$1 or CMos or MOS))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
8	BRS	L8	823	diode same ((second or plurality) adj (pFET$1 or transistor$1 or CMos or MOS)) same (nFET or (n or npn or (n adj channel)) near transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB